



Discrete Power MOSFETs

onsemi PSG/MPD

June. 2025

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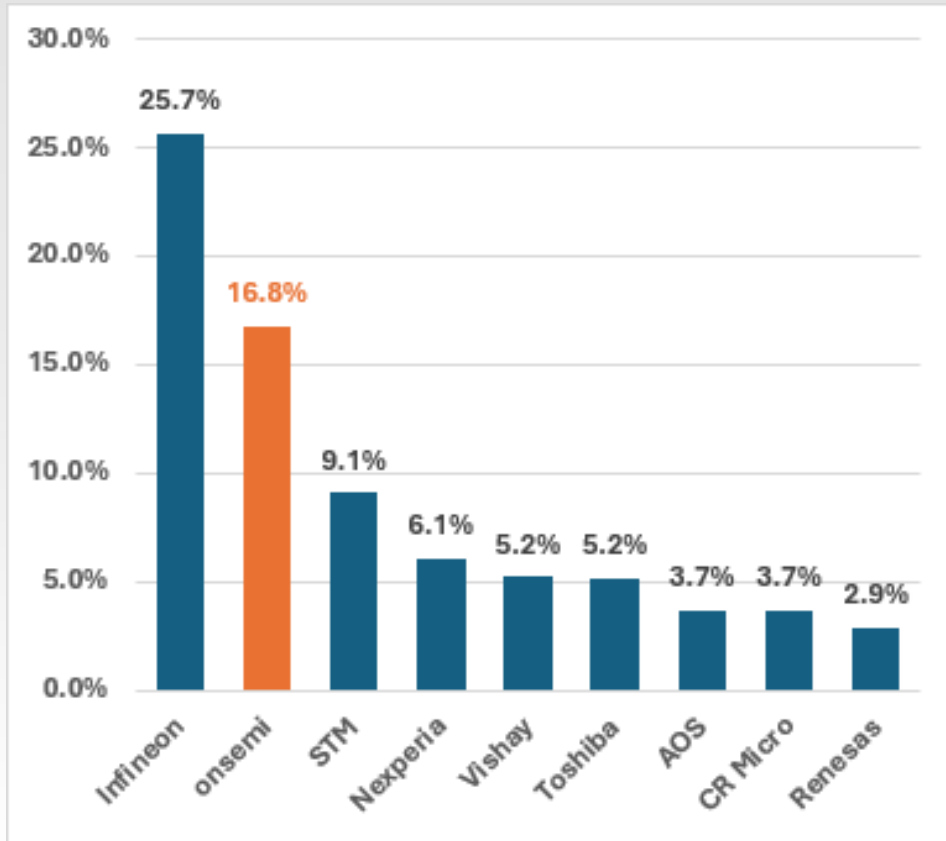
A detailed, futuristic illustration of a cityscape built upon a dark, textured circuit board. The city features several tall, glowing orange skyscrapers, a yellow robotic arm, and various other electronic components like capacitors and resistors. The scene is lit with warm orange and yellow light, creating a bokeh effect in the background.

MOSFET Share, Advantage, and Manufacturing Capabilities

Market Share & onsemi's Advantage

- Market Share
- LV and MV MOSFETs

Source : Omdia



onsemi's Advantage

- Broad MOSFET Portfolio 8V ~ 1000V
- Enabling 300mm capability at East Fishkill
- Invest in advanced silicon technologies to achieve competitive differentiation
- Invest to expand competitive advantage in power packages
- Expand capacity for power products, 15% annual growth
- Embed quality in every system, tool and process with detailed attention to providing best-in-class products and solutions.

Formidable Manufacturing Capabilities

- Scale provides industry leading cost structure, 50 billion units shipped in 2023
- Front-end capabilities key source of competitive advantage in power and analog
- Substrate internal capacity for silicon 150 mm and 200 mm, and SiC 150 mm
- Front-end internal capacity to manufacture 150 mm, 200 mm and 300 mm silicon, and 150 mm SiC
- Back-end internal capacity to assemble and ship Discretes, integrated circuits (ICs) and modules world-wide
- One of world's largest and most efficient back-end operations (~1 billion units every week)

Front-end & Substrate Facilities

Aizu, Japan



Czech Republic Fab



Czech Rep. Substrates



Bucheon, Korea



Seremban, Malaysia



Gresham, OR, USA



East Fishkill, NY, USA



Mountain Top, PA, USA



Hudson, NH, USA



Back-end Facilities

Leshan, China



Suzhou, China



Shenzhen, China



Seremban, Malaysia



Vietnam OSBD



Carmona, Philippines



Tarlac, Philippines



Cebu, Philippines



Burlington, Canada



Vietnam OPP/IPM



MMPS Alignment to Corporate Strategy

Industrial

Automation (Robots, AGV)

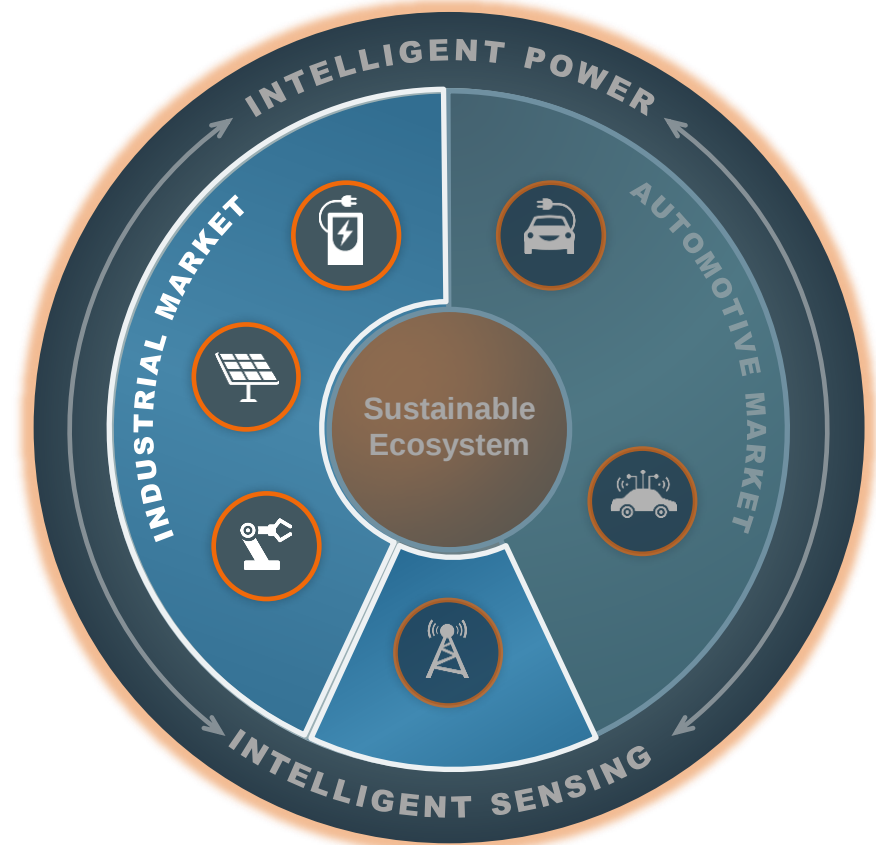
Renewables

Power Tools/Equipment

Cloud Power

5G Infrastructure

Data Centers



The background of the slide is a futuristic, high-tech circuit board. It features various components like microchips, capacitors, and a small robotic arm. The lighting is warm and orange, with glowing lines and patterns that suggest advanced technology and data flow. The overall aesthetic is sleek and modern.

Technology Overview

T10 Technology Value Proposition

- 30% ~ 40% Rsp Reduction (v.s. pre-art) → To achieve higher power density for compact system design.
- 2x Reduction on Qg, Qsw, Qoss (v.s. pre-art) → To reduce switching loss for higher efficiency requirement.
- Excellent Body-Diode Softness (v.s. pre-art) → To reduce voltage stress for less EMI & noise issue.
- 10% Increase UIS Capability (v.s. pre-art) → To achieve higher reliability and robustness system requirement.

T10 Optimized Technology

T10S

Switching DC-DC Applications

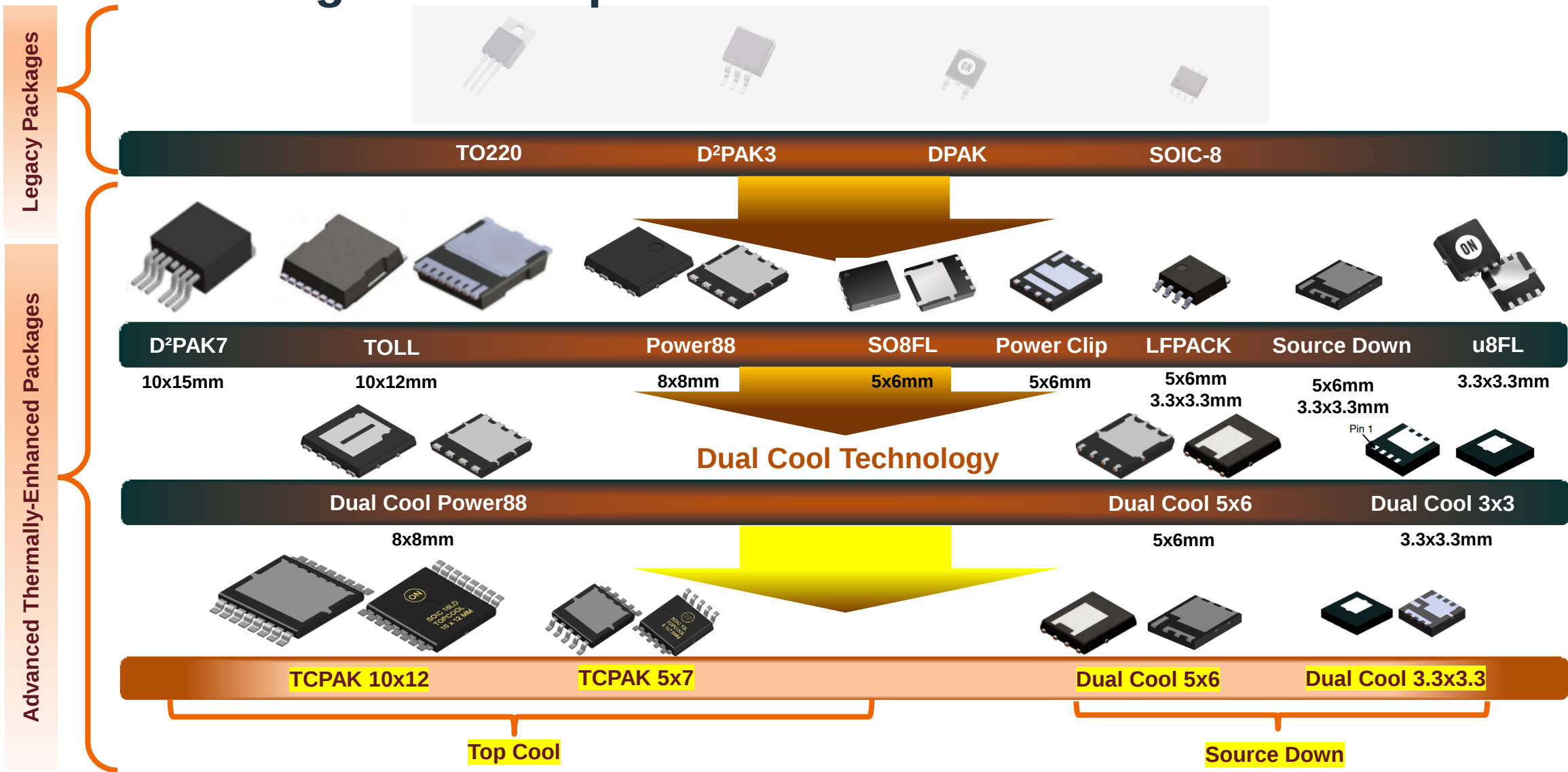
- Lower Qg, - Less driving loss
- Lower Qsw – Less switching loss
- Lower Qoss – Less charge/discharge loss
- Lower Qrr – Less reverse recovery loss

T10M

Motor Drive Applications

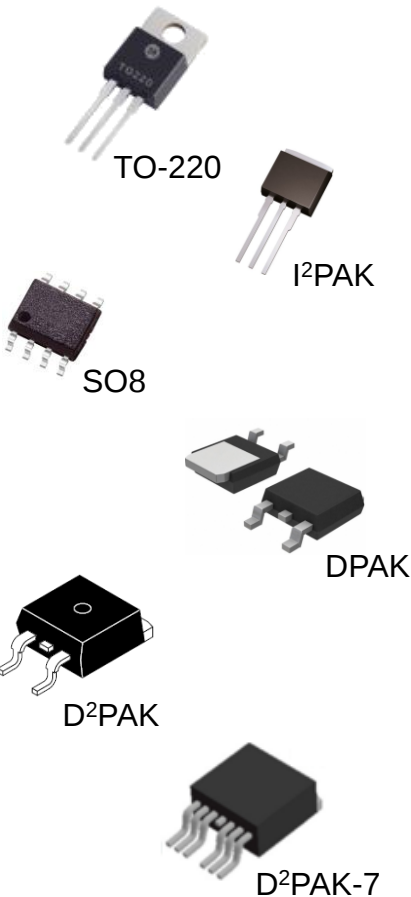
- Lower rDS(on), - Less conduction loss
- Lower Qg – Less driving loss
- Excellent Body-Diode Softness – Less voltage spike
- Higher UIS Capability – More reliable

Power Package Roadmap

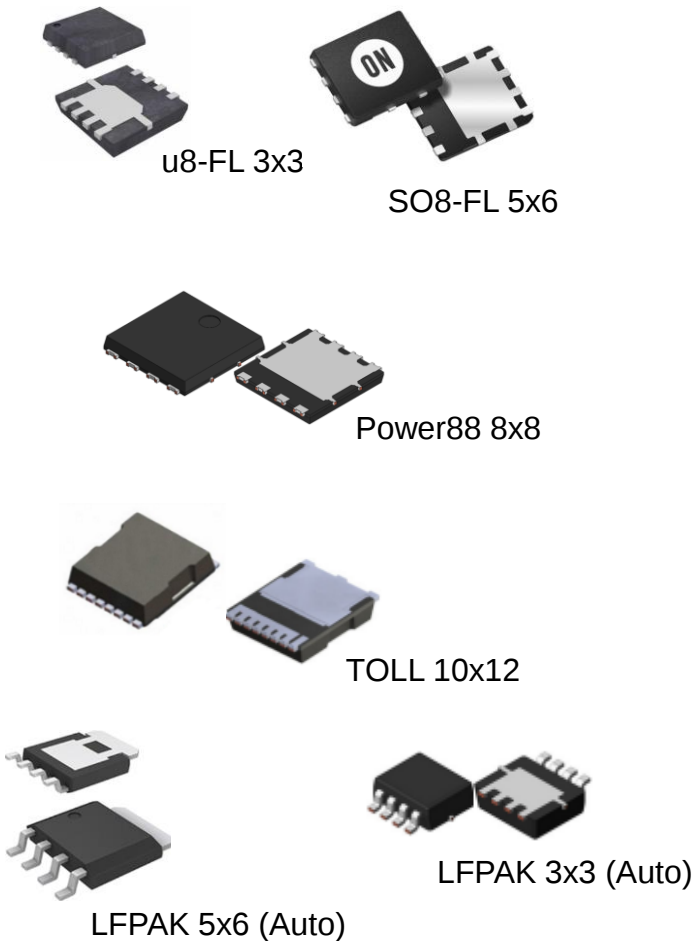


Discrete Power Packages Trend

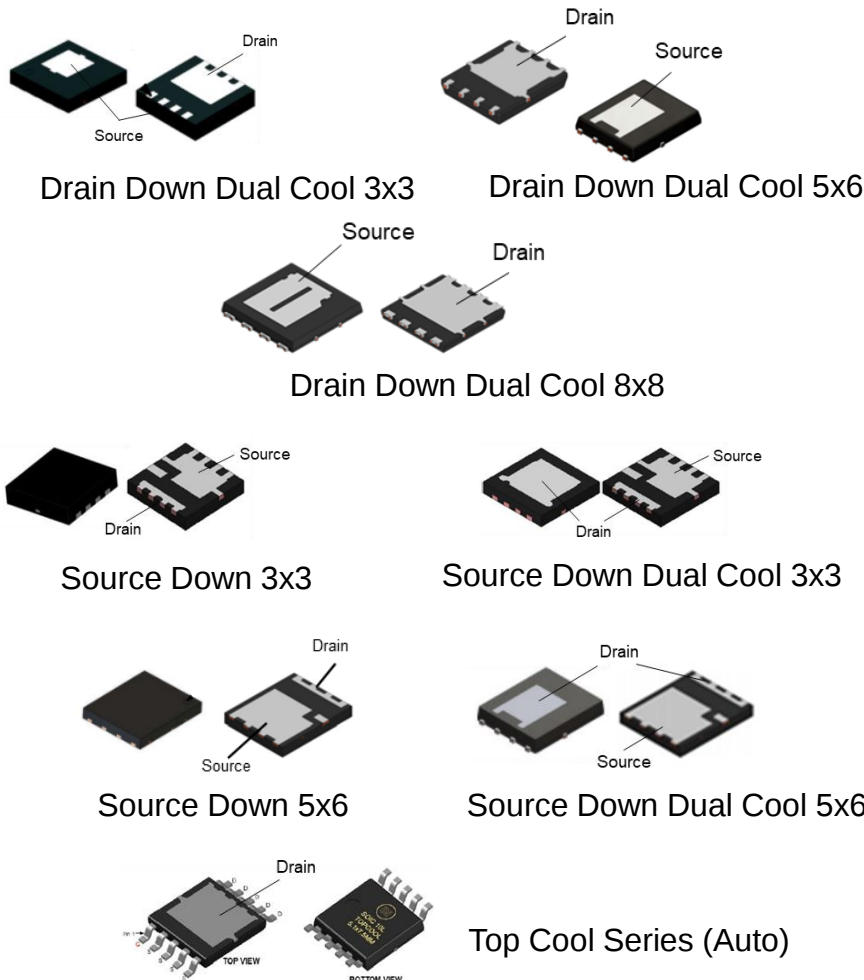
Legacy



High Density



Advanced - Higher Thermal Performance



The background of the slide is a futuristic, high-tech image of a circuit board. It features glowing orange and yellow components, including a robotic arm and a structure labeled "AI". The overall aesthetic is dark and high-tech, with a blue and orange color scheme.

Cloud / Datacenter & Server Target Application

High Performance Silicon MOSFET Major Applications



Cloud / Datacenter & Server

High-performance,
High-power density required

Applications: (AC/DC, DC/DC Power Converters)

- 48Vo Power Supply Unit (Datacenter)
- 48Vi (IBC) Intermediate Bus Converter, DC/DC
- 12Vo Power Supply Unit (Server)
- Hot-swap

Technology: 25V/PT11E, T10, 30V/T6, T10,
40V/T10S, 80V/T10,
Package: 3x3 & 5x6, Source-Down, Dual-Cool

25V, 40V,
80V

30V, 40V,
80V, 100V,
120V, 150V

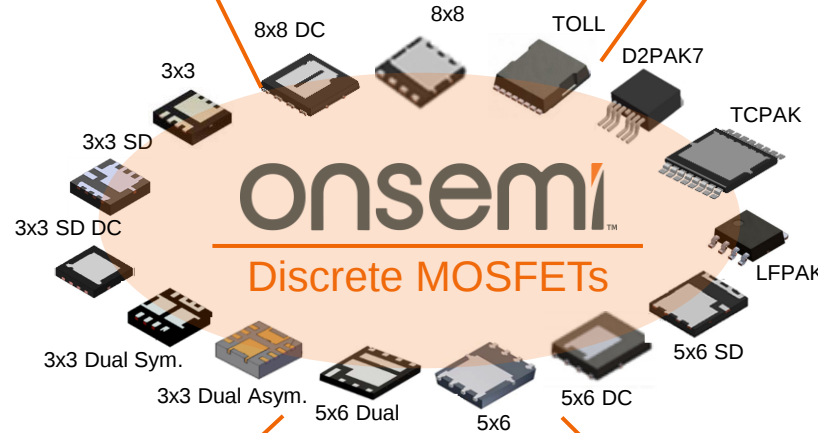
Battery-Powered Applications

High-robustness,
High-thermal performance ability required

Applications: (Motor Drive)

- Power Tools
- Battery pack
- Forklift
- E-Bike

Technology: 30V/T6, T10, 40V/T10M, 80V/T10, 120V/PTNG,
150V/PTNG
Package: 5x6, 8x8, TOLL, D2PAK7, TCPAK, Dual-Cool



5G Infrastructure

High-performance,
High-reliability required

Applications: (AC/DC, DC/DC Power Converters)

- 54Vo Power Supply Unit
- 36Vi~75Vi DC/DC Bricks
- Hot-swap

Technology: 60V/T6, T8, T10, 80V/T10, 100V/PTNG LowQsw, T10S, 120V/PTNG,
150V/PTNG
Package: 5x6, Source-Down, Dual-Cool, TCPAK

60V, 80V,
100V, 120V,
150V,

60V, 80V,
100V, 150V,

Renewable Energy

Application: (DC/AC Inverter)

- Solar Optimizer
- Micro-Inverter

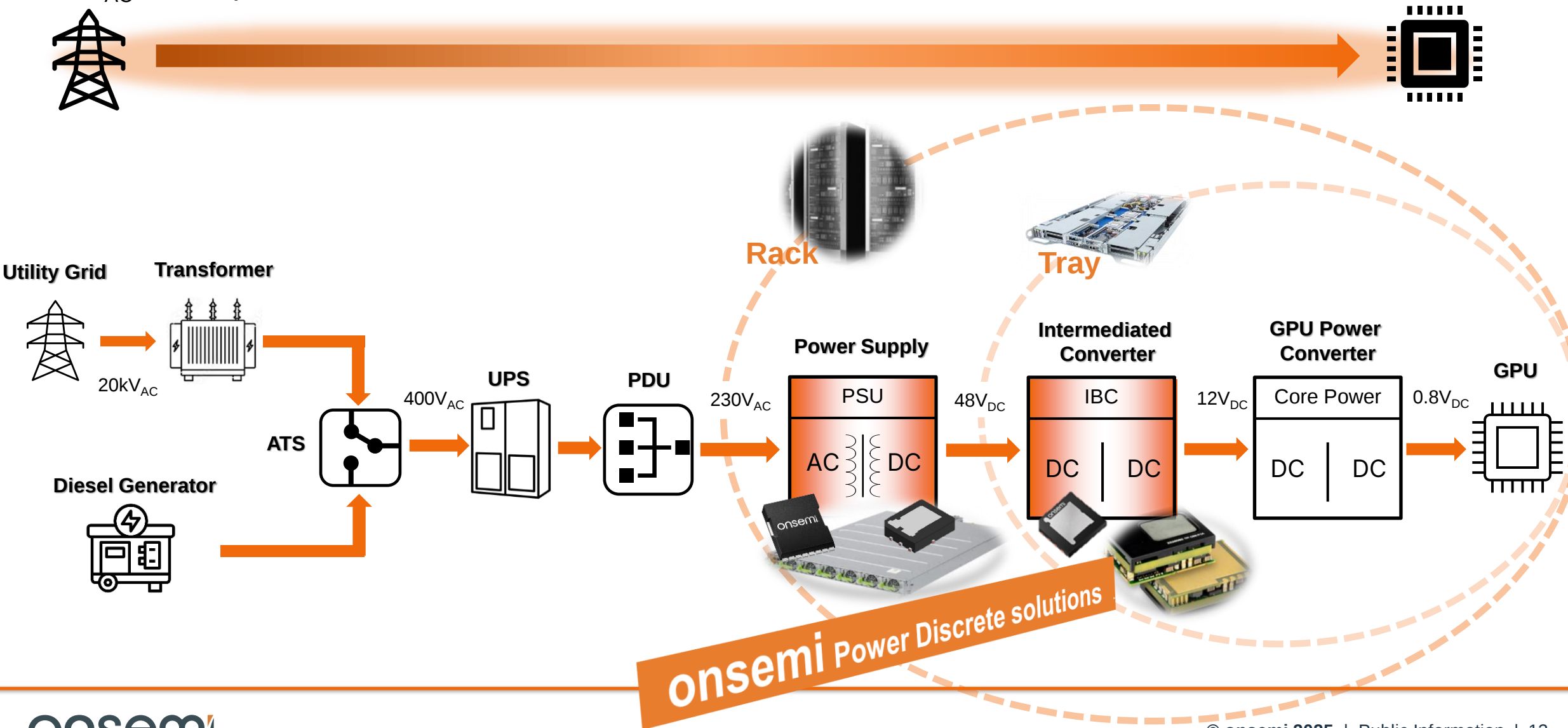
Technology: 60V/T6, T8, T10, 80V/T10, 100V/PTNG LowQsw, T10S,
150V/PTNG
Package: 5x6, Source-Down, Dual-Cool, TCPAK



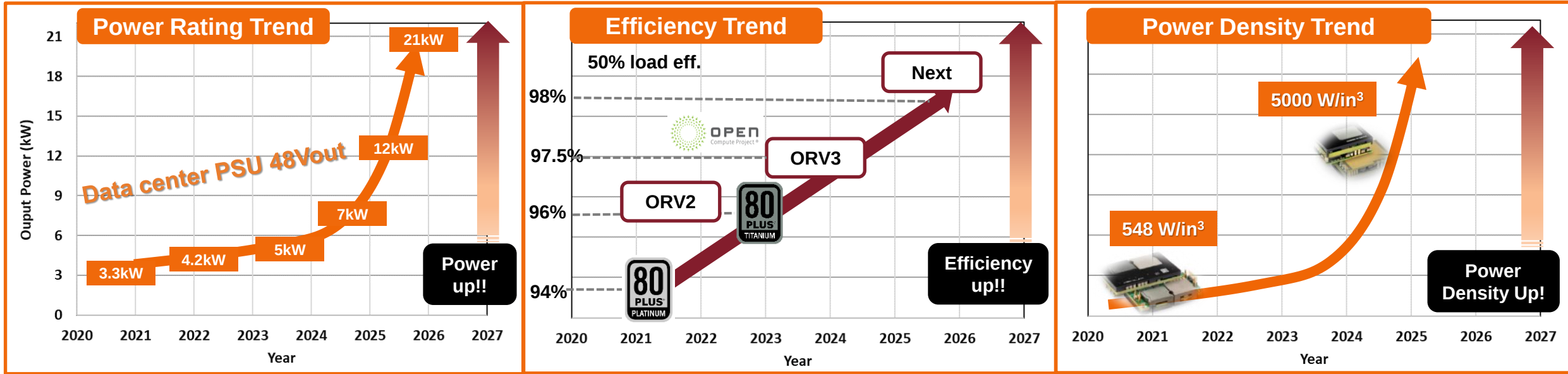
Power Delivery from Grid to GPU in Data Center

20k V_{AC} – Grid power

0.8V_{DC} – GPU power



Power Delivery Trend – Power Rating, Efficiency, and Density



Power Semiconductors Challenges:

Higher current density is required.
Higher switching performance is required.
Higher thermal performance is required.

Higher Efficiency
&
Higher Power Density !

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T10 Technology

T10 Technology Value Proposition

More Efficient, Powerful, and Reliable Solution



T10 Optimized Technology



T10S

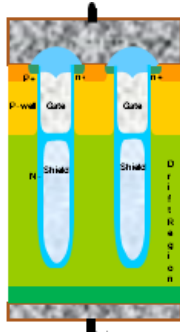
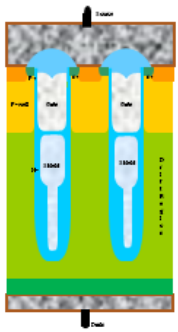
Fast Switching DC-DC Applications

- Improved FOM – Higher efficiency
- Lower Qg - Less driving loss
- Lower Qsw – Less switching loss
- Lower Qoss – Less charge/discharge loss
- Lower Qrr – Less reverse recovery loss

T10M

Motor Control Applications

- Tighter Vth Variation
- Lower RDS(on) - Less conduction loss
- Lower Qg – Less driving loss
- Excellent Body-Diode Softness – Less voltage spike
- Higher UIS Capability – More reliable



T10 80V product portfolio

Product	Gate	Package	Configuration	VDSS (V)	VGS (V)	VGS(th) Min (V)	VGS(th) Max (V)	ID Max (A)	RDS(on) Max VGS = 4.5V (mΩ)	RDS(on) Max VGS = 10V (mΩ)	Qg Typ VGS = 4.5V (nC)	Qg Typ VGS = 10V (nC)	Ciss Typ (pF)	Technology	Status
NTMFSCH1D4N08X	SG	Power 56 Dual Cool	Single	80	±20	2.4	3.6	283		1.4		88	6280	T10	Development
NTBLS0D8N08X	SG	Power 1012 (TOLL)	Single	80	±20	2.4	3.6	457		0.79		174	12920	T10	Released
NTTFS5D6N08XL	LL	Power 33 (u8FL)	Single	80	±20	1.5	2.1	79	8.4	5.3	17	28	1800	T10	Released
NTMFSC1D9N08X	SG	Power 56 Dual Cool	Single	80	±20	2.4	3.6	201		1.9		63	4470	T10	Development
NTMFWS1D5N08X	SG	Power 56 (SO-8FL)	Single	80	±20	2.4	3.6	253		1.43		83	5880	T10	Released
NTMFS2D1N08X	SG	Power 56 (SO-8FL)	Single	80	±20	2.4	3.6	201		1.9		63	4470	T10	Released
NTMFS2D5N08X	SG	Power 56 (SO-8FL)	Single	80	±20	2.4	3.6	181		2.1		53	3800	T10	Released
NTMFS3D0N08X	SG	Power 56 (SO-8FL)	Single	80	±20	2.4	3.6	154		2.6		45	3200	T10	Released
NTMFS3D5N08X	SG	Power 56 (SO-8FL)	Single	80	±20	2.4	3.6	135		3		38	2680	T10	Released
NTMFS4D0N08X	SG	Power 56 (SO-8FL)	Single	80	±20	2.4	3.6	119		3.5		33	2400	T10	Released
NTMFS4D5N08X	SG	Power 56 (SO-8FL)	Single	80	±20	2.4	3.6			4.5		24	1714	T10	Released
NTMFS6D2N08X	SG	Power 56 (SO-8FL)	Single	80	±20	2.4	3.6			6.2		19	1346	T10	Released
NTMFSC2D6N08X	SG	Power 56 Dual Cool	Single	80	±20	2.4	3.6	154		2.6		45	3200	T10	Development
NTTFS5H4D0N08XL	LL	Power 33 Source Down	Single	80	±20	1.5	2.1	107	5.3	3.6	19	40	2520	T10S	Development
NTTFS5SCH4D0N08XL	LL	Power 33 Dual Cool Source Down	Single	80	±20	1.5	2.1	107	5.3	3.6	19	40	2520	T10S	Released

T10 40V product portfolio

Product	Gate	Package	Configuration	VDSS (V)	VGS (V)	VGS(th) Min (V)	VGS(th) Max (V)	ID Max (A)	RDS(on) Max VGS = 4.5V (mΩ)	RDS(on) Max VGS = 10V (mΩ)	Qg Typ VGS = 4.5V (nC)	Qg Typ VGS = 10V (nC)	Ciss Typ (pF)	Technology	Status
NTTFSSCH1D3N04XL	LL	Power 33 Dual Cool Source Down	Single	40	±20	1.3	2.2	204	1.7	1.3	21	47	3480	T10S	Released
NTTFSSH1D3N04XL	LL	Power 33 Source Down	Single	40	±20	1.3	2.2	204	1.7	1.3	21	47	3480	T10S	Released
NTTFS1D4N04XM	SG	Power 33 (u8FL)	Single	40	±20	2.5	3.5	178		1.43		35.4	2278	T10M	Released
NTMFSCH0D4N04XM	SG	Power 56 Dual Cool	Single	40	±20	2.5	3.5	529		0.4		142	9143	T10M	Development
NTMFS0D4N04XM	SG	Power 56 (SO-8FL)	Single	40	±20	2.5	3.5	509		0.42		133	8577	T10M	Released
NTMFS0D5N04XL	LL	Power 56 (SO-8FL)	Single	40	±20	1.3	2.2	455	0.78	0.49	57	127	9444	T10S	Released
NTMFS0D5N04XM	SG	Power 56 (SO-8FL)	Single	40	±20	2.5	3.5	414		0.52		97.5	6267	T10M	Released
NTMFS0D7N04XM	SG	Power 56 (SO-8FL)	Single	40	±20	2.5	3.5	323		0.7		72.1	4621	T10M	Released
NTMFS0D7N04XL	LL	Power 56 (SO-8FL)	Single	40	±20	1.3	2.2	349	1.1	0.7	42	96	7090	T10S	Released
NTMFSC0D8N04XM	SG	Power 56 Dual Cool	Single	40	±20	2.5	3.5	310		0.78		72.1	5044	T10M	Released
NTMFS0D9N04XM	SG	Power 56 (SO-8FL)	Single	40	±20	2.5	3.5	273		0.9		61	3918	T10M	Released
NTMFS0D9N04XL	LL	Power 56 (SO-8FL)	Single	40	±20	1.3	2.2	278	1.5	0.9	31	70	5160	T10S	Released
NTMFS1D1N04XM	SG	Power 56 (SO-8FL)	Single	40	±20	2.5	3.5	233		1.05		49.1	3155	T10M	Released
NTMFS1D3N04XM	SG	Power 56 (SO-8FL)	Single	40	±20	2.5	3.5	195		1.3		38.5	2473	T10M	Released
NTMFS1D7N04XM	SG	Power 56 (SO-8FL)	Single	40	±20	2.5	3.5	151		1.8		28.7	1844	T10M	Released
NTMFS2D3N04XM	SG	Power 56 (SO-8FL)	Single	40	±20	2.5	3.5	111		2.35		22.1	1421	T10M	Released
NTMFS3D1N04XM	SG	Power 56 (SO-8FL)	Single	40	±20	2.5	3.5	83		3.1		15.6	1002	T10M	Released
NTMFS4D7N04XM	SG	Power 56 (SO-8FL)	Single	40	±20	2.5	3.5	66		4.7		10.4	668	T10M	Released
NTTFS4D9N04XM	SG	Power 33 (u8FL)	Single	40	±20	2.5	3.5	65		4.9		10.4	668	T10M	Released

T10 25V/30V product portfolio

Product	Gate	Package	Configuration	VDSS (V)	VGS (V)	ID Max (A)	RDS(on) Max VGS = 4.5V (mΩ)	RDS(on) Max VGS = 10V (mΩ)	Qg Typ VGS = 4.5V (nC)	Qg Typ VGS = 10V (nC)	Ciss Typ (pF)	Technology	Status
NTMFD1D1N02X	LL	PQFN-8	Dual	25	+16 / -12	75, 178	3.75, 1.1	3, 0.87	6.8, 27	15, 27	1080, 4265	T10	Released
NTMFS0D3N03X	LL	Power 56 (SO-8FL)	Single	30	±20	567		0.31		155	12014	T10	Development
NTMFS0D6N03X	LL	Power 56 (SO-8FL)	Single	30	±20	358		0.53		83	6416	T10	Development
NTTFSSH0D7N02X	LL	Power 33 Source Down	Single	25	-12/+16	310	0.8	0.58	25	55	3980	T10	Released
NTTFSSCH0D7N02X	LL	Power 33 Dual Cool Source Down	Single	25	-12/+16	310	0.8	0.58	25	55	3980	T10S	Released

The background of the slide is a futuristic, high-tech circuit board. It features various components like capacitors, resistors, and integrated circuits, all illuminated with a warm, orange-gold glow. A prominent feature is a small, yellow robotic arm with a gripper, positioned on the right side of the board. The overall aesthetic is sleek and modern, representing advanced semiconductor technology.

T6 and T8 Technolog 60V and 80V

T6 MOSFET Portfolio (60V) – 3x3mm and 5x6mm Packages

Features and Benefits

- Low RDS(on) → Improve System Efficiency
- Low Capacitance and Gate Charge → Improve Switching Losses
- Advanced Power 5x6mm and 3x3 Packages → Improve Thermal Performance

Application

- DC-DC
- Motor Drive
- Oring / Power Load Switch / Protection



Product	Package	Dimensions (mm)	Config.	VDSS (V)	VGS Max (V)	VGS(th) Max (V)	ID Max (A)	RDS(on) Max VGS = 4.5V (mΩ)	RDS(on) Max VGS = 10V (mΩ)	Qg Typ VGS = 10V (nC)	Ciss Typ (pF)
NTTFS5C670NL	WDFN-8 / u8FL	3x3	Single	60	±20	2	70	9.1	6.5	20	1400
NTTFS5C673NL	WDFN-8 / u8FL	3x3	Single	60	±20	2	50	13.3	9.3	9.5	880
NTMFS5C604N	SO-8FL / DFN-5	5x6	Single	60	±20	4	280		1.2	80	6400
NTMFS5C604NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	276	1.7	1.2	120	8900
NTMFS5C612NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	226	2.3	1.5	91	6660
NTMFS5C612N	SO-8FL / DFN-5	5x6	Single	60	±20	4	230		1.6	60.2	4830
NTMFS5C628NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	150	3.3	2.4	52	3600
NTMFS5C628N	SO-8FL / DFN-5	5x6	Single	60	±20	4	150		3	34	2630
NTMFS5C645NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	100	5.7	4	34	2200
NTMFS5C645N	SO-8FL / DFN-5	5x6	Single	60	±20	4	94		4.5	20.4	1510
NTMFS5C646NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	89	6.3	4.7	33.7	2164
NTMFS5C670NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	71	8.8	6.1	20	1400
NTMFS5C673NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	50	13	9.2	9.5	880
NTMFS5C677NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	36	21.5	15	9.7	620
NTMFD5C650NL	SO-8FL Dual	5x6	Dual	60	±20	2.2	111	5.8	4.2	37	2546
NTMFD5C672NL	SO-8FL Dual	5x6	Dual	60	±20	2.2	49	16.8	11.9	12.3	793
NTMFD5C674NL	SO-8FL Dual	5x6	Dual	60	±20	2.2	42	20.4	14.4	10	640
NTMFD5C680NL	SO-8FL Dual	5x6	Dual	60	±20	2.2	26	41	28	5	350

T8 MOSFET Portfolio (60V & 80V) - 3x3mm and 5x6mm Packages

Features and Benefits

Low RDS(on) → Improve System Efficiency

Low Capacitance and Gate Charge → Improve Switching Losses

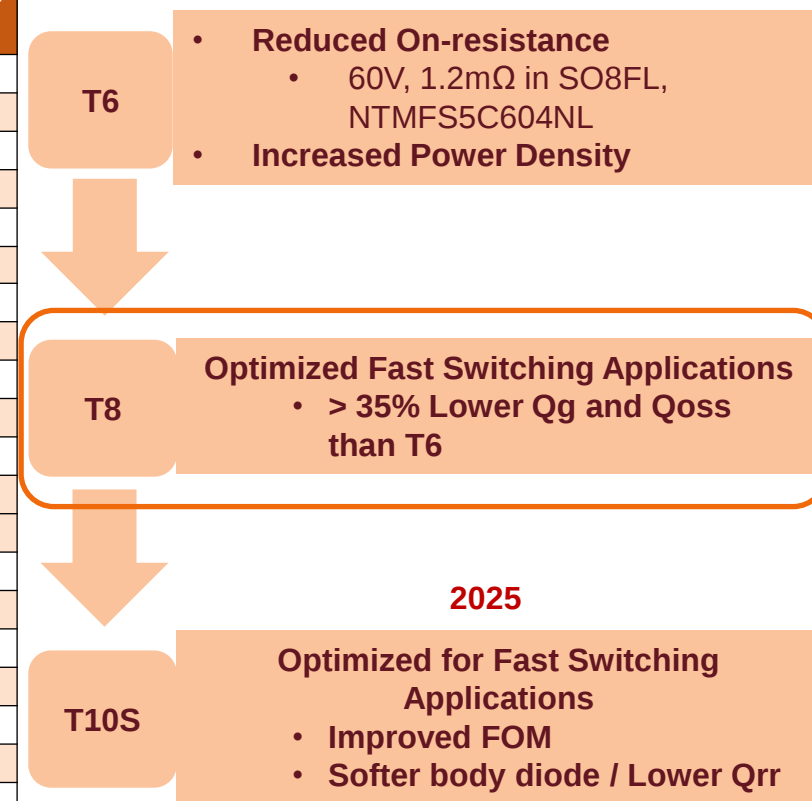
Advanced Power 5x6mm and 3x3 Packages → Improve Thermal Performance

Application

- Soft-Switching DC-DC



Technology Roadmap



Product	Package	Dimensions (mm)	Config.	VDSS (V)	VGS Max (V)	VGS(th) Max (V)	ID Max (A)	RDS(on) Max VGS = 4.5V (mΩ)	RDS(on) Max VGS = 10V (mΩ)	Qg Typ VGS = 10V (nC)	Ciss Typ (pF)
NTTFS5D1N06HL	WDFN-8 / u8FL	3x3	Single	60	±20	2	78	7.1	5.2	22.5	1610
NTMFS5H600NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	250	1.7	1.3	89	6680
NTMFS5H615NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	200	2.5	1.8	62	4860
NTMFS5H630NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	120	4.4	3.1	35	2540
NTTFS3D7N06HL	PQFN-8	5x6	Single	60	±20	2	103	5.2	3.9	32.7	2383
NTMFS5H663NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	61	10	7.2	17	1131
NTMFS5H610NL	SO-8FL / DFN-5	5x6	Single	60	±20	2	47	13	10	13	880
NTTFS5D9N08H	WDFN-8 / u8FL	3x3	Single	80	±20	4	84		5.9	31	2040
NTTFS8D1N08H	WDFN-8 / u8FL	3x3	Single	80	±20	4	61		8.3	23	1450
NTTFS6H850NL	WDFN-8 / u8FL	3x3	Single	80	±20	2	64	11	8.6	26	1450
NTTFS6H850N	WDFN-8 / u8FL	3x3	Single	80	±20	4	68		9.5	19	1140
NTTFS6H854NL	WDFN-8 / u8FL	3x3	Single	80	±20	2	41	17.3	13.4	17	902
NTMFS6H800NL	SO-8FL / DFN-5	5x6	Single	80	±20	3.5	224	2.4	1.8	112	6900
NTMFS6H801NL	SO-8FL / DFN-5	5x6	Single	80	±20	2	160	3.3	2.7	90	5126
NTMFS6H818N	SO-8FL / DFN-5	5x6	Single	80	±20	4	123		3.7	46	3100
NTMFS6H824N	SO-8FL / DFN-5	5x6	Single	80	±20	4	103		4.5	38	2470
NTMFS6D1N08H	SO-8FL / DFN-5	5x6	Single	80	±20	4	89		5.5	32	2085
NTMFS6H836NL	SO-8FL / DFN-5	5x6	Single	80	±20	2	77	7.8	6.2	34	1950
NTMFS6H848NL	SO-8FL / DFN-5	5x6	Single	80	±20	2	59	11	8.8	25	1420
NTMFS6H852NL	SO-8FL / DFN-5	5x6	Single	80	±20	2	42	17	13.1	17	906

The background of the slide is a futuristic, high-tech circuit board. It features various components like capacitors, resistors, and integrated circuits, all rendered in a dark blue and orange color scheme. A prominent feature is a large, glowing orange structure that resembles a stylized 'E' or a series of vertical bars, with a small orange robotic arm positioned next to it. The overall aesthetic is sleek and modern, with a focus on advanced technology.

150V Portfolio

150V MOSFET Solution

Product	Package	Dimensions (mm)	Channel Polarity	VDSS (V)	VGS (V)	VGS(th) Min (V)	VGS(th) Max (V)	ID Max (A)	RDS(on) Max VGS = 10V (mΩ)	Qg Typ VGS = 10V (nC)	Ciss Typ (pF)	Coss Typ (pF)	Crss Typ (pF)	Qrr Typ (nC)
NTTFS022N15MC	PQFN-8	3x3	N-Channel	150	±20	2.5	4.5	37.2	22	17	1315	380	6	155
NTTFS034N15MC	PQFN-8	3x3	N-Channel	150	±20	2.5	4.5	27	31	12	905	270	5	126
FDMC86260	PQFN-8	3x3	N-Channel	150	±20	2	4	25	34	9.7	1000	105	4.8	85
NTTFD9D0N06HL	WQFN-12	3x3	N-Channel	150	±20	1.2	2	38	9	13.5	948	188	12.3	14
NTMFSC012N15MC	DFN8 Dual Cool	5x6	N-Channel	150	±20	2.5	4.5	80	11.4	32.4	2490	676	9	559
FDMS86200DC	DFN-8 Dual Cool	5x6	N-Channel	150	±20	2	4	40	17	19	2110	205	8.1	126
FDMS8D8N15C	PQFN-8	5x6	N-Channel	150	±20	2.5	4.5	85	8.8	38	3132	927	5.3	108
NTMFS011N15MC	PQFN-8	5x6	N-Channel	150	±20	2	4.5	78	11.5	30.7	2478	728	7.9	227
FDMS86255	PQFN-8	5x6	N-Channel	150	±20	2	4	45	12.4	29	3200	291	11	165
FDMS86200	PQFN-8	5x6	N-Channel	150	±20	2	4	35	18	18	2041	203	10	113
NTMFS022N15MC	PQFN-8	5x6	N-Channel	150	±20	2.5	4.5	41.9	22	17	1315	380	6	155
FDMS86250	PQFN-8	5x6	N-Channel	150	±20	2	4	30	25	14	1750	165	8.8	112
NTMFS034N15MC	PQFN-8	5x6	N-Channel	150	±20	2.5	4.5	31	31	12	905	270	5	126
NTMTS4D3N15MC	DFNW-8	8x8	N-Channel	150	±20	2	4.5	174	4.45	79	6514	1750	12.5	194
NTMTSC4D3N15MC	DFNW-8	8x8	N-Channel	150	±20	2	4.5	174	4.45	79	6514	1750	12.5	194
NTMTS6D0N15MC	DFNW-8	8x8	N-Channel	150	±20	2	4.5	135	6.4	58	4815	1482	9.7	125
NTMFS7D5N15MC	PQFN-8	8x8	N-Channel	150	±20	2.5	4.5	95.6	7.9	46	3835	1070	11	111
NTMFS015N15MC	PQFN-8	8x8	N-Channel	150	±20	2.5	4.5	61	14	27	2120	595	10.5	197
FDMT800150DC	PQFN-8 Dual Cool	8x8	N-Channel	150	±20	2	4	99	6.5	77	5660	520	17	233
FDMT800152DC	PQFN-8 Dual Cool	8x8	N-Channel	150	±20	2	4	72	9	38	4196	379	16	187
NTBLS4D0N15MC	TOLL 8L	10x11	N-Channel	150	±20	2	4.5	187	4.4	90.4	7490	2055	27.2	180
FDBL0630N150	TOLL 8L	10x11	N-Channel	150	±20	2	4	169	6.3	70	5805	536	16	323



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